

Sergey A Mintairov

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

176
papers

1,016
citations

16
h-index

24
g-index

193
ext. papers

1,177
ext. citations

1.1
avg, IF

4.09
L-index

#	Paper	IF	Citations
176	On-chip light detection using integrated microdisk laser and photodetector bonded onto Si board. <i>Laser Physics Letters</i> , 2022 , 19, 016201	1.5	0
175	Dynamic characteristics and noise modelling of directly modulated quantum well-dots microdisk lasers on silicon. <i>Laser Physics Letters</i> , 2022 , 19, 025801	1.5	
174	Material gain of InGaAs/GaAs quantum well-dots. <i>Semiconductor Science and Technology</i> , 2021 , 36, 0150088		4
173	Piezo-electric fields and state-filling photo-luminescence in natural InP/GaInP2 Wigner molecule structures. <i>Applied Physics Letters</i> , 2021 , 118, 121101	3.4	2
172	Effect of the Active Region and Waveguide Design on the Performance of Edge-Emitting Lasers Based on InGaAs/GaAs Quantum Well-Dots. <i>Semiconductors</i> , 2021 , 55, 333-340	0.7	0
171	Near-field magneto-photoluminescence of GaAs/AlGaAs/InP/GaInP2 quantum well-quantum dot structures. <i>Journal of Physics: Conference Series</i> , 2021 , 1851, 012015	0.3	
170	Improved performance of InGaAs/GaAs microdisk lasers epi-side down bonded onto a silicon board. <i>Optics Letters</i> , 2021 , 46, 3853-3856	3	6
169	Temperature dependencies of the refractive index for Al-Ga-In-As metamorphic layers. <i>Optics Letters</i> , 2021 , 46, 4928-4931	3	
168	Increasing the Efficiency of 520- to 540-nm Laser Radiation Photovoltaic Converters Based on GaInP/GaAs Heterostructures. <i>Technical Physics Letters</i> , 2021 , 47, 290-292	0.7	
167	Energy Consumption at High-Frequency Modulation of an Uncooled InGaAs/GaAs/AlGaAs Microdisk Laser. <i>Technical Physics Letters</i> , 2021 , 47, 685-688	0.7	
166	Formation of Heterostructures of GaP/Si Photoconverters by the Combined Method of MOVPE and PEALD. <i>Technical Physics Letters</i> , 2021 , 47, 730-733	0.7	
165	Influence of QD array positioning in GaAs solar cell p-n junction on their photoelectric characteristics. <i>Journal of Physics: Conference Series</i> , 2021 , 2103, 012192	0.3	
164	Temperature stability of small-signal modulation response of WGM microlasers with InGaAs/GaAs quantum well-dots in the active region. <i>Journal of Physics: Conference Series</i> , 2021 , 2086, 012082	0.3	
163	The Influence of the Number of Rows of GaInAs Quantum Objects on the Saturation Current of GaAs Photoconverters. <i>Technical Physics Letters</i> , 2020 , 46, 599-602	0.7	0
162	Laser Power Converter Modules with a Wavelength of 809850 nm. <i>Technical Physics</i> , 2020 , 65, 1690-1694.5		
161	Effects of Doping of Bragg Reflector Layers on the Electrical Characteristics of InGaAs/GaAs Metamorphic Photovoltaic Converters. <i>Semiconductors</i> , 2020 , 54, 476-483	0.7	1
160	Experimental and Theoretical Examination of the Photosensitivity Spectra of Structures with In _{0.4} Ga _{0.6} As Quantum Well-Dots of the Optical Range (900-1050 nm). <i>Technical Physics Letters</i> , 2020 , 46, 203-206	0.7	3

159	Finding the Energy Gap of Ga _{1-x} In _x As p-n Junctions on a Metamorphic Buffer from the Photocurrent Spectrum. <i>Technical Physics Letters</i> , 2020 , 46, 332-334	0.7	1
158	Light Emitting Devices Based on Quantum Well-Dots. <i>Applied Sciences (Switzerland)</i> , 2020 , 10, 1038	2.6	20
157	Ultimate Lasing Temperature of Microdisk Lasers. <i>Semiconductors</i> , 2020 , 54, 677-681	0.7	2
156	Photovoltaic converters with quantum objects under laser flux of subband photons. <i>Journal of Physics: Conference Series</i> , 2020 , 1697, 012189	0.3	
155	The study of voltage loss reasons in GaAs solar cells with embedded InGaAs quantum dots. <i>Journal of Physics: Conference Series</i> , 2020 , 1695, 012078	0.3	
154	High-Speed Photodetectors for the 950-1000 nm Optical Range Based on In _{0.4} Ga _{0.6} As/GaAs Quantum Well-Dot Nanostructures. <i>Technical Physics Letters</i> , 2020 , 46, 1219-1222	0.7	0
153	The GaAs laser photoconverter (809 nm) current flow mechanisms at the temperature range of 100-420 K. <i>Journal of Physics: Conference Series</i> , 2020 , 1697, 012170	0.3	
152	Micro-photoluminescence of InP/GaInP ₂ quantum dots structures for topological quantum gates. <i>Journal of Physics: Conference Series</i> , 2020 , 1697, 012201	0.3	
151	Investigation of microdisk and microring lasers based on InGaAs/GaAs QWDs by the interferometry method. <i>Journal of Physics: Conference Series</i> , 2020 , 1695, 012093	0.3	
150	Analysis of the lasing characteristics of InGaAs/GaAs WGM microlasers. <i>Journal of Physics: Conference Series</i> , 2020 , 1695, 012096	0.3	
149	Gain spectra of lasers based on transitional dimension active region. <i>Journal of Physics: Conference Series</i> , 2020 , 1697, 012177	0.3	
148	Tuning of laser power converters efficiency by means of temperature. <i>Journal of Physics: Conference Series</i> , 2020 , 1697, 012191	0.3	1
147	Experimental investigation of the far-field emission pattern of microdisk laser modes. <i>Journal of Physics: Conference Series</i> , 2020 , 1695, 012094	0.3	
146	Isotype barriers in the connecting part of multi-junction solar cells. <i>Journal of Physics: Conference Series</i> , 2020 , 1695, 012091	0.3	
145	The dependence of recombination in GaAs solar cells on the number of included GaInAs quantum objects. <i>Journal of Physics: Conference Series</i> , 2020 , 1695, 012092	0.3	
144	InGaAs metamorphic laser power converters with distributed Bragg reflector for wavelength range 0.8-1.1 μm 2020 ,		2
143	Comparative analysis of the optical and physical properties of InAs and In _{0.8} Ga _{0.2} As quantum dots. <i>Journal of Physics: Conference Series</i> , 2020 , 1697, 012107	0.3	1
142	Electronic states in GaAs photoconverters with InGaAs quantum well-dots. <i>Applied Physics Express</i> , 2020 , 13, 015009	2.4	3

141	Study of GaP Nucleation Layers Grown on Si by Plasma-Enhanced Atomic Layer Deposition. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2020 , 217, 1900532	1.6	1
140	Impact of Self-Heating and Elevated Temperature on Performance of Quantum Dot Microdisk Lasers. <i>IEEE Journal of Quantum Electronics</i> , 2020 , 56, 1-8	2	8
139	Optimization of photoelectric parameters of InGaAs metamorphic laser ($\lambda=1064\text{nm}$) power converters with over 50% efficiency. <i>Solar Energy Materials and Solar Cells</i> , 2020 , 217, 110710	6.4	11
138	The Effect of Self-Heating on the Modulation Characteristics of a Microdisk Laser. <i>Technical Physics Letters</i> , 2020 , 46, 515-519	0.7	4
137	Temperature Tweaking of the Output Photovoltaic Parameters of Laser Power Converters. <i>IEEE Electron Device Letters</i> , 2020 , 41, 1324-1327	4.4	6
136	Comparative Analysis of the Optical and Physical Properties of InAs and In _{0.8} Ga _{0.2} As Quantum Dots and Solar Cells Based on them. <i>Semiconductors</i> , 2020 , 54, 1267-1275	0.7	1
135	A Micro Optocoupler Based on a Microdisk Laser and a Photodetector with an Active Region Based on Quantum Well-Dots. <i>Technical Physics Letters</i> , 2020 , 46, 629-632	0.7	0
134	Energy Consumption for High-Frequency Switching of a Quantum-Dot Microdisk Laser. <i>Technical Physics Letters</i> , 2019 , 45, 847-849	0.7	3
133	Evaluation of energy-to-data ratio of quantum-dot microdisk lasers under direct modulation. <i>Journal of Applied Physics</i> , 2019 , 126, 063107	2.5	10
132	Dethermalization of carriers in GaAs solar cells with quantum objects. <i>Applied Physics Express</i> , 2019 , 12, 035005	2.4	4
131	Transverse mode competition in narrow-ridge diode lasers. <i>Laser Physics</i> , 2019 , 29, 025003	1.2	1
130	Module of Laser-Radiation ($\lambda=1064\text{nm}$) Photovoltaic Converters. <i>Semiconductors</i> , 2019 , 53, 1110-1113	0.7	2
129	Lasers Based on Quantum Well-Dots Emitting in the 980- and 1080-nm Optical Ranges. <i>Technical Physics Letters</i> , 2019 , 45, 163-166	0.7	1
128	Evaluation of the Impact of Surface Recombination in Microdisk Lasers by Means of High-Frequency Modulation. <i>Semiconductors</i> , 2019 , 53, 1099-1103	0.7	1
127	Photovoltage-induced blockade of charge and spin diffusion in semiconducting thin films. <i>Journal of Applied Physics</i> , 2019 , 126, 025701	2.5	1
126	Thermal and resistive losses in InGaAs metamorphic laser ($\lambda=1064\text{nm}$) power converters with over 50% efficiency 2019 ,		8
125	Time-Resolved Photoluminescence of InGaAs Nanostructures Different in Quantum Dimensionality. <i>Semiconductors</i> , 2019 , 53, 1489-1495	0.7	2
124	High speed data transmission using directly modulated microdisk lasers based on InGaAs/GaAs quantum well-dots. <i>Optics Letters</i> , 2019 , 44, 5442-5445	3	14

123	Direct modulation characteristics of microdisk lasers with InGaAs/GaAs quantum well-dots. <i>Photonics Research</i> , 2019 , 7, 664	6	16
122	Anomalies in Photovoltaic Characteristics of Multijunction Solar Cells at Ultrahigh Solar Light Concentrations. <i>Technical Physics Letters</i> , 2019 , 45, 1100-1102	0.7	3
121	Specific Features of the Current-Voltage Characteristic of Microdisk Lasers Based on InGaAs/GaAs Quantum Well-Dots. <i>Technical Physics Letters</i> , 2019 , 45, 994-996	0.7	6
120	The effect of post-growth interruption on the formation of InGaAs/GaAs quantum dots obtained by MOVPE. <i>Journal of Physics: Conference Series</i> , 2019 , 1400, 055015	0.3	1
119	High-power 0.98 μm range diode lasers based on InGaAs/GaAs quantum well-dot active region. <i>Journal of Physics: Conference Series</i> , 2019 , 1400, 066045	0.3	1
118	Performance of InGaAs metamorphic laser power converters at different conditions. <i>Journal of Physics: Conference Series</i> , 2019 , 1410, 012094	0.3	0
117	Spectral method for determining quantum wells thickness and the composition in strained heterostructures GaAs/InGaAs. <i>Journal of Physics: Conference Series</i> , 2019 , 1410, 012095	0.3	
116	Spectral analysis of the electroluminescence and photoresponse of heterostructures with InGaAs quantum objects. <i>Journal of Physics: Conference Series</i> , 2019 , 1410, 012099	0.3	
115	Experimental study of power-limiting factors of 1.1 μm range edge-emitting lasers based on InGaAs/GaAs quantum well-dot nanostructures. <i>Journal of Physics: Conference Series</i> , 2019 , 1410, 012100 ^{0.3}	0.3	
114	Transverse mode switching in quantum well-dot lasers triggered by gain saturation. <i>Journal of Physics: Conference Series</i> , 2019 , 1410, 012118	0.3	
113	Relation between energy gap and saturation currents in GaInAs homo p-n junctions. <i>Journal of Physics: Conference Series</i> , 2019 , 1410, 012097	0.3	1
112	Counteracting the Photovoltaic Effect in the Top Intergenerator Part of GaInP/GaAs/Ge Solar Cells. <i>Semiconductors</i> , 2019 , 53, 1535-1539	0.7	1
111	On modelling optical parameters of InAs quantum dots for cascade GaInP / GaAs / Ge solar cells. <i>Journal of Physics: Conference Series</i> , 2019 , 1400, 066058	0.3	
110	Filling of In(Ga)P/GaInP quantum dot electron states detected by microphotoluminescence. <i>Journal of Physics: Conference Series</i> , 2019 , 1400, 077013	0.3	1
109	Investigation of optical properties of In(Ga)As/GaAs mesa structures with active region based on quantum wells, quantum dots, and quantum well-dots. <i>Journal of Physics: Conference Series</i> , 2019 , 1410, 012157	0.3	2
108	Increasing the Photocurrent of a Ga(In)As Subcell in Multijunction Solar Cells Based on GaInP/Ga(In)As/Ge Heterostructure. <i>Technical Physics Letters</i> , 2019 , 45, 1258-1261	0.7	0
107	Bimodality in Arrays of In _{0.4} Ga _{0.6} As Hybrid Quantum-Confined Heterostructures Grown on GaAs Substrates. <i>Semiconductors</i> , 2018 , 52, 53-58	0.7	6
106	Gradual Evolution From Quantum-Well-Like to Quantum-Dot-Like Characteristics in InGaAs/GaAs Nanostructures. <i>Physica Status Solidi (B): Basic Research</i> , 2018 , 255, 1800123	1.3	6

105	Density Control of InP/GaInP Quantum Dots Grown by Metal-Organic Vapor-Phase Epitaxy. <i>Semiconductors</i> , 2018 , 52, 497-501	0.7	1
104	Bragg reflectors for measuring optical parameters of layers of metamorphic InAlGaAs/GaAs heterostructures. <i>Optics Express</i> , 2018 , 26, A832-A843	3.3	2
103	In _{0.8} Ga _{0.2} As Quantum Dots for GaAs Solar Cells: Metal-Organic Vapor-Phase Epitaxy Growth Peculiarities and Properties. <i>Semiconductors</i> , 2018 , 52, 870-876	0.7	2
102	Heterointerfaces in the bottom tunnel part of GaInP/GaAs/Ge solar cells. <i>Journal of Physics: Conference Series</i> , 2018 , 1124, 041028	0.3	
101	Optical and electrical properties of superlattice and photonic metamorphic structures for high-performance solar cells 2018 ,		2
100	Series spreading resistance in single- and multi-junction concentrator solar cells. <i>Journal of Physics: Conference Series</i> , 2018 , 1038, 012105	0.3	1
99	Heating of photovoltaic converter by laser beam: overheating temperature. <i>Journal of Physics: Conference Series</i> , 2018 , 1135, 012070	0.3	3
98	Investigation of Alloyed Ohmic Contacts in Epitaxial Tellurium-Doped Gallium Arsenide Layers. <i>Russian Microelectronics</i> , 2018 , 47, 388-392	0.5	1
97	Effect of carrier localization on performance of coupled large optical cavity diode lasers. <i>Journal of Physics: Conference Series</i> , 2018 , 1124, 041005	0.3	1
96	Edge-emitting lasers based on transitionally dimensional InGaAs/GaAs active region. <i>Journal of Physics: Conference Series</i> , 2018 , 1135, 012071	0.3	4
95	Investigation of InAs/InGaP nano-heterostructures grown by MOVPE for intermediate band solar cells. <i>Journal of Physics: Conference Series</i> , 2018 , 1124, 022030	0.3	
94	Optical properties of In _{0.8} Ga _{0.2} As quantum dots in GaAs photovoltaic convertors. <i>Journal of Physics: Conference Series</i> , 2018 , 1124, 041003	0.3	
93	Modeling of the internal quantum yield for solar cell with quantum dots.. <i>Journal of Physics: Conference Series</i> , 2018 , 1124, 041030	0.3	
92	A novel approach to characterization of bottom sub-cell in multijunction solar cell using photoluminescence.. <i>Journal of Physics: Conference Series</i> , 2018 , 1124, 041039	0.3	
91	Reducing of thermal resistance of edge-emitting lasers based on coupled waveguides. <i>Journal of Physics: Conference Series</i> , 2018 , 1124, 041016	0.3	1
90	Electro-optical properties of InAs and In _{0.8} Ga _{0.2} As quantum dots in GaAs solar cells. <i>Journal of Physics: Conference Series</i> , 2018 , 1135, 012078	0.3	1
89	An Antireflection Coating of a Germanium Subcell in GaInP/GaAs/Ge Solar Cells. <i>Technical Physics Letters</i> , 2018 , 44, 1042-1044	0.7	1
88	InAs quantum dots for cascade GaInP / GaAs / Ge solar cells. <i>Journal of Physics: Conference Series</i> , 2018 , 1135, 012077	0.3	

87	Diode Lasers with Near-Surface Active Region. <i>Semiconductors</i> , 2018 , 52, 1901-1904	0.7	
86	Optical Properties of InGaAs/InAlAs Metamorphic Nanoheterostructures for Photovoltaic Converters of Laser and Solar Radiation. <i>Technical Physics Letters</i> , 2018 , 44, 877-880	0.7	1
85	The investigation of InGaAs quantum dot growth peculiarities for GaAs intermediate band solar cells. <i>Journal of Physics: Conference Series</i> , 2018 , 1038, 012110	0.3	2
84	Photoconverter heating by incident radiation: Overheat temperature and IV-curve correction 2018 ,		4
83	InGaAs/GaAs receiver for infrared (1064 nm) laser power conversion 2018 ,		2
82	Power Characteristics and Temperature Dependence of the Angular Beam Divergence of Lasers with a Near-Surface Active Region. <i>Technical Physics Letters</i> , 2018 , 44, 675-677	0.7	1
81	Current localization in heterostructures of multijunction solar cells: Causes for arising and diagnostics potential 2018 ,		1
80	InGaAs metamorphic laser (1064 nm) power converters with over 44% efficiency 2018 ,		8
79	Reduction of Internal Loss and Thermal Resistance in Diode Lasers with Coupled Waveguides. <i>Semiconductors</i> , 2018 , 52, 1462-1467	0.7	2
78	Highly efficient injection microdisk lasers based on quantum well-dots. <i>Optics Letters</i> , 2018 , 43, 4554-4557		39
77	Edge-emitting and microdisk lasers based on hybrid quantum-well-dot structures 2018 ,		1
76	Recombination in GaAs p-i-n Structures with InGaAs Quantum-Confined Objects: Modeling and Regularities. <i>Semiconductors</i> , 2018 , 52, 1244-1248	0.7	4
75	Multilayer Quantum Well-Dot InGaAs Heterostructures in GaAs-based Photovoltaic Converters. <i>Semiconductors</i> , 2018 , 52, 1249-1254	0.7	1
74	Control of Wigner localization and electron cavity effects in near-field emission spectra of In(Ga)P/GaN quantum-dot structures. <i>Physical Review B</i> , 2018 , 97,	3.3	13
73	InGaAs metamorphic laser (1064 nm) power converters with over 40% efficiency. <i>Electronics Letters</i> , 2017 , 53, 173-175	1.1	18
72	Optimization of structural and growth parameters of metamorphic InGaAs photovoltaic converters grown by MOCVD. <i>Semiconductors</i> , 2017 , 51, 93-99	0.7	14
71	Light-emitting and photovoltaic devices based on quantum well-dots hybrid nanostructures 2017 ,		2
70	InGaAs quantum well-dots based GaAs subcell with enhanced photocurrent for multijunction GaInP/GaAs/Ge solar cells. <i>Semiconductor Science and Technology</i> , 2017 , 32, 015006	1.8	12

69	InAs quantum dots grown by MOCVD in GaAs and metamorphic InGaAs matrixes. <i>Journal of Physics: Conference Series</i> , 2017 , 816, 012024	0.3	1
68	Investigation of lasers based on coupled waveguides by near-field scanning optical microscopy. <i>Journal of Physics: Conference Series</i> , 2017 , 929, 012070	0.3	
67	InAs QDs in a metamorphic In _{0.25} Ga _{0.75} As matrix, grown by MOCVD. <i>Semiconductors</i> , 2017 , 51, 672-678	0.7	
66	Optical properties of hybrid quantum-well dots nanostructures grown by MOCVD. <i>Semiconductors</i> , 2017 , 51, 357-362	0.7	2
65	InGaAs/GaAs hybrid quantum well-dot nanostructures: Impact of substrate orientation and recombination mechanisms. <i>Journal of Physics: Conference Series</i> , 2017 , 917, 032001	0.3	3
64	Edge-emitting lasers based on coupled large optical cavity with high beam stability. <i>Journal of Physics: Conference Series</i> , 2017 , 929, 012077	0.3	
63	Experimental studies of the effects of atomic ordering in epitaxial Ga _x In _{1-x} P alloys on their structural and morphological properties. <i>Semiconductors</i> , 2017 , 51, 1087-1092	0.7	1
62	Manifestation of counteracting photovoltaic effect on IV characteristics in multi-junction solar cells. <i>Journal of Physics: Conference Series</i> , 2017 , 917, 052034	0.3	
61	Current mismatch violation in concentrator multijunction solar cells 2017 ,		3
60	Optical properties of hybrid quantum-confined structures with high absorbance. <i>Semiconductors</i> , 2016 , 50, 1180-1185	0.7	2
59	Photovoltaic laser-power converter based on AlGaAs/GaAs heterostructures. <i>Semiconductors</i> , 2016 , 50, 1220-1224	0.7	32
58	Temperature characteristics of tilted wave lasers. <i>Optical Engineering</i> , 2016 , 55, 116102	1.1	
57	Near-field scanning magneto-optical spectroscopy of Wigner molecules 2016 ,		3
56	Current flow mechanism in GaAs solar cells with GaInAs quantum dots 2016 ,		9
55	Optimization of structural and growth parameters of metamorphic InGaAs/GaAs photoconverters grown by MOCVD. <i>Journal of Physics: Conference Series</i> , 2016 , 741, 012086	0.3	5
54	Heterostructures of metamorphic GaInAs photovoltaic converters fabricated by MOCVD on GaAs substrates. <i>Semiconductors</i> , 2016 , 50, 517-522	0.7	10
53	Simulation of the ohmic loss in photovoltaic laser-power converters for wavelengths of 809 and 1064 nm. <i>Semiconductors</i> , 2016 , 50, 125-131	0.7	13
52	Optical mode engineering and high power density per facet length (>8.4 kW/cm) in tilted wave laser diodes 2016 ,		8

51	Increasing the quantum efficiency of InAs/GaAs QD arrays for solar cells grown by MOVPE without using strain-balance technology. <i>Progress in Photovoltaics: Research and Applications</i> , 2016 , 24, 1261-1271	6.8	34
50	Increasing the quantum efficiency of GaAs solar cells by embedding InAs quantum dots. <i>Journal of Physics: Conference Series</i> , 2016 , 769, 012036	0.3	
49	GaIn intermixing, intrinsic doping, and Wigner localization in the emission spectra of self-organized InP/GaInP quantum dots. <i>Journal Physics D: Applied Physics</i> , 2016 , 49, 475301	3	15
48	TEM Analysis of InGaAs/GaAs Quantum Well-Quantum Dot Structures for Optoelectronics Applications. <i>Microscopy and Microanalysis</i> , 2016 , 22, 1256-1257	0.5	
47	Counter-photo-electromotive force at heterointerfaces in MJ SC: Study by spectral method 2016 ,		6
46	Metamorphic InGaAs photo-converters on GaAs substrates. <i>Journal of Physics: Conference Series</i> , 2016 , 690, 012032	0.3	2
45	On current spreading in solar cells: a two-parameter tube model. <i>Semiconductors</i> , 2016 , 50, 970-975	0.7	4
44	Comparison of wet chemical treatment and Ar-ion sputtering for GaInP ₂ (100) surface preparation. <i>Materials Science in Semiconductor Processing</i> , 2016 , 51, 81-88	4.3	6
43	Estimation of the potential efficiency of a multijunction solar cell at a limit balance of photogenerated currents. <i>Semiconductors</i> , 2015 , 49, 668-673	0.7	10
42	Transverse single-mode edge-emitting lasers based on coupled waveguides. <i>Optics Letters</i> , 2015 , 40, 2150-2	3	18
41	Determination of the technological growth parameters in the InAs-GaAs system for the MOCVD synthesis of Multimodal InAs QDs. <i>Semiconductors</i> , 2015 , 49, 1111-1118	0.7	10
40	Site-Controlled Growth of Single InP QDs. <i>Semiconductors</i> , 2015 , 49, 1095-1098	0.7	
39	GaAs quantum well-dots solar cells with spectral response extended to 1100nm. <i>Electronics Letters</i> , 2015 , 51, 1602-1604	1.1	29
38	Heterointerfaces in MJ SC: IV curves and their peculiarities 2015 ,		3
37	Passive cavity laser and tilted wave laser for Bessel-like beam coherently coupled bars and stacks 2015 ,		4
36	The Segmental Approximation in Multijunction Solar Cells. <i>IEEE Journal of Photovoltaics</i> , 2015 , 5, 1229-1236	3.6	19
35	Hybrid InGaAs quantum well-dots nanostructures for light-emitting and photo-voltaic applications. <i>Nanotechnology</i> , 2015 , 26, 385202	3.4	34
34	Effect of the bimodality of a QD array on the optical properties and threshold characteristics of QD lasers. <i>Semiconductors</i> , 2015 , 49, 1090-1094	0.7	10

33	Single-Mode Emission From 49-nm Microdisk Lasers With Dense Array of InGaAs Quantum Dots. <i>Journal of Lightwave Technology</i> , 2015 , 33, 171-175	4	8
32	Subtractive method for obtaining the dark current-voltage characteristic and its types for the residual (nongenerating) part of a multi-junction solar cell. <i>Semiconductors</i> , 2014 , 48, 653-658	0.7	2
31	Characterization of the Manufacturing Processes to Grow Triple-Junction Solar Cells. <i>International Journal of Photoenergy</i> , 2014 , 2014, 1-10	2.1	13
30	AlGaAs/GaAs photovoltaic converters for high power narrowband radiation 2014 ,		16
29	High intensity low temperature (HILT) performance of space concentrator GaInP/GaInAs/Ge MJ SCs 2014 ,		4
28	High differential efficiency tilted wave laser 2014 ,		1
27	Picosecond internal Q-switching mode correlates with laser diode breakdown voltage. <i>Semiconductors</i> , 2013 , 47, 406-408	0.7	
26	Spectral-splitting concentrator photovoltaic modules based on AlGaAs/GaAs/GaSb and GaInP/InGaAs(P) solar cells. <i>Technical Physics</i> , 2013 , 58, 1034-1038	0.5	9
25	Local triboelectrification of an n-GaAs surface using the tip of an atomic-force microscope. <i>Semiconductors</i> , 2013 , 47, 1170-1173	0.7	6
24	Influence of the position of InGaAs quantum dot array on the spectral characteristics of AlGaAs/GaAs photovoltaic converters. <i>Technical Physics Letters</i> , 2012 , 38, 1024-1026	0.7	1
23	Interface properties of GaInP/Ge hetero-structure sub-cells of multi-junction solar cells. <i>Journal Physics D: Applied Physics</i> , 2012 , 45, 495305	3	11
22	Photoelectric determination of the series resistance of multijunction solar cells. <i>Semiconductors</i> , 2012 , 46, 1051-1058	0.7	11
21	Multijunction solar cell with intermediate IR reflector 2012 ,		3
20	Lasing of whispering-gallery modes in GaInP waveguide micro-discs and rings with InP quantum dots. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2011 , 8, 325-327		15
19	Characterization of GaInP/Ge heterostructure solar cells by capacitance measurements at forward bias under illumination. <i>Energy Procedia</i> , 2011 , 3, 76-83	2.3	4
18	Improvement of Radiation Resistance of Multijunction GaInP/Ga(In)As/Ge Solar Cells with Application of Bragg Reflectors. <i>Advances in Science and Technology</i> , 2010 , 74, 225-230	0.1	3
17	AlGaAs/GaAs Photovoltaic Cells with InGaAs Quantum Dots. <i>Advances in Science and Technology</i> , 2010 , 74, 231-236	0.1	12
16	Quantum Hall regime in emission spectra of single self-organized InP/GaInP quantum dots. <i>Journal of Physics: Conference Series</i> , 2010 , 245, 012041	0.3	2

15	Study of minority carrier diffusion lengths in photoactive layers of multijunction solar cells. <i>Semiconductors</i> , 2010 , 44, 1084-1089	0.7	14
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13	Multijunction GaInP/GaInAs/Ge solar cells with Bragg reflectors. <i>Semiconductors</i> , 2010 , 44, 1600-1605	0.7	10
12	Edge-emitting InGaAs/GaAs laser with high temperature stability of wavelength and threshold current. <i>Semiconductor Science and Technology</i> , 2010 , 25, 045003	1.8	4
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9	AlGaAs/GaAs photovoltaic cells with an array of InGaAs QDs. <i>Semiconductors</i> , 2009 , 43, 514-518	0.7	125
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